

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/706,971	11/14/2003	Takaei Sasaki	101136-00102	7505	
7:	590 08/02/2005		EXAM	INER	
ARENT FOX KINTNER PLOTKIN & KAHN, PLLC			ROSASCO, STEPHEN D		
SUITE 400 1050 CONNEC	CTICUT AVENUE, N.W.	•	ART UNIT	ART UNIT PAPER NUMBER	
	N, DC 20036-5339		1756 DATE MAILED: 08/02/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

			<i>′</i>
	Application No.	Applicant(s)	
Office Action Commence	10/706,971	SASAKI ET AL.	
Office Action Summary	Examiner	Art Unit	
	Stephen Rosasco	1756	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the o	orrespondence address -	-
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tir within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communica D (35 U.S.C. § 133).	ition.
Status			
Responsive to communication(s) filed on <u>04 Not</u> This action is FINAL . 2b)⊠ This Since this application is in condition for allowar closed in accordance with the practice under E	action is non-final.		s is
Disposition of Claims			
4) ☐ Claim(s) 15-18 is/are pending in the application 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 15-18 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or Application Papers 9) ☐ The specification is objected to by the Examine 10) ☐ The drawing(s) filed on 04 November 2003 is/are	vn from consideration. r election requirement.	ed to by the Evaminer	
Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex	drawing(s) be held in abeyance. Se ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.12	• •
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applications have been received in Applications of the contract	on No. <u>09/361,158</u> . ed in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 11/04/03	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:		

U.S. Patent and Trademark Office PTOL-326 (Rev. 1-04)

Detailed Action

The disclosure is objected to because of the following informalities: the specification should be amended to include the update of the stats of the parent application.

"This application is a divisional application which claims the benefit of pending application Serial No. 09/361,158, filed July 27, 1999, which is now U.S. Patent No. 6,685,848. The disclosure of the prior application is hereby incorporated herein by reference in its entirety. --

Appropriate correction is required.

Drawings

Figure 1 and 2 should be designated by a legend such as --prior Art- because only that which is old is illustrated. See MPEP j 608.02(g). Corrected drawings in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. The replacement sheets) should be labeled "Replacement Sheet" in the page header (as per 37 CFR 1.84(c)) so as not to obstruct any portion of the drawing figures. If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 15-18 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Application/Control Number: 10/706,971

Art Unit: 1756

Claims 15·16 · The claims are directed to a method for manufacturing a semiconductor circuit, but the last lines of the claims recite that the patterns can be formed on a wafer or to manufacture a semiconductor circuit. The preamble does not include patterning a wafer as an end in itself. Therefore, these claims are unclear.

Claims 15-18. The phrase "such as" in the claims "pattern-forming steps such as...", renders the claim indefinite because the limitations following this phrase are rendered optional and it is unclear whether these limitations are part of the claimed invention. See MPEP ç 2173.05(d).

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 15-18 are rejected under 35 U.S.C. 102(b) as being anticipated by Isao et al. (5,629,114).

The claimed invention is directed to a method of manufacturing a semiconductor circuit and a semiconductor circuit product made by the process, and claimed as a product by process claim. The claimed methods include the use of a dry-etching method which comprises the step of dry-etching a metal thin film as a chromium-containing half-tone phase-shift film, wherein the method is characterized by using, as an etching gas, a mixed gas including (a) a reactive ion etching gas, which contains an oxygen-containing gas and a halogen-containing gas, and (b) a reducing gas added to the gas component (a), in the

Page 4

process for dry-etching the metal thin film. The dry-etching method permits the production of a half-tone phase-shift photomask by forming patterns to be transferred to a wafer on a photomask blank for a chromium-containing half-tone phase-shift mask. The photomask can in turn be used for manufacturing semiconductor circuits. The method is directed to the decrease of the dimensional difference due to the coexistence of coarse and dense patterns in a plane and the production of a high precision pattern-etched product.

Isao et al. teach a method of manufacturing a phase shift mask, which method comprises: sputtering a phase shifter film of a prescribed thickness on a substrate, said phase shifter film consisting of a single material having a phase of transmitted exposure light converted by 180 degree and having transmittance of 5% to 40%;

forming a resist film having a prescribed pattern on the phase shifter film; and dry etching said phase shifter film using the resist film as a mask to form a first light transmit portion having said substrate exposed and a second light transmit portion made of said phase shifter film;

wherein said single material is selected from the group consisting of an oxide of a metal, a nitride oxide of a metal, an oxide of a metal silicide and a nitride oxide of a metal silicide.

And comprising sputtering a phase shifter film of an oxide of molybdenum silicide using a target of molybdenum silicide in a mixed gas atmosphere of argon and oxygen.

And comprising dry etching said phase shifter film with a mixed gas of carbon fluoride and oxygen.

Art Unit: 1756

comprising sputtering a phase shifter film of a nitride oxide of molybdenum silicide using a target of molybdenum silicide in a mixed gas atmosphere of argon, oxygen and nitrogen.

The method can also comprise dry etching said phase shifter film with a gas selected from the group consisting of a mixed gas of methylene chloride and oxygen, a mixed gas of choline and oxygen, and a choline gas.

Conclusion

Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Stephen Rosasco whose telephone number is (571) 272-1389. The Examiner can normally be reached Monday Friday, from 8:00 AM to 4:30 PM. The Examiner's supervisor, Mark Huff, can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

S. Rosasco

Primary Examiner

Art Unit 1756

S.Rosasco 07/26/05